

ABSTRACT

A method of manufacturing a gate, a thin film transistor and a pixel. First, a patterned mask layer is formed on a substrate. The mask layer exposes an area for forming the gate. A gate is formed on the exposed area of the substrate and then the mask layer is removed. The method produces a gate having a well-defined profile. When the method is applied to form a transistor or a pixel, coverage of a subsequently form film layer is improved and point discharge is prevented.